

Assignment - 1
CMOS Logic Design
EE 671 - VLSI Design



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EE 671: VLSI Design
Assignment 1

Due on
Aug. 21, 2023

We want to design a CMOS inverter using a 180 nm CMOS process. The n and p channel transistors in this process have a channel length of $0.18\mu\text{m}$ and a minimum channel width of $0.24\mu\text{m}$. The supply voltage for logic design is 1.8V. Transistor models for this process are attached in a separate file called models-180nm.

Design an inverter in this process with a load capacitance of 0.05pF. In addition to this capacitance, the capacitances associated with the inverter transistors themselves should be included in the design. For this, the source/drain area and perimeter values (which depend on transistor geometry) should be given to the simulator. These parameters can be calculated as shown in the figure below.

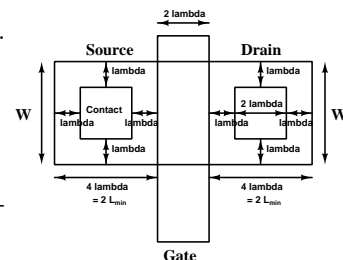
Width of either diffused region is W while its length is 4λ .

Since $\lambda = L_{\min}/2$, $4\lambda = 2L_{\min}$, the Source/Drain area is given by $as = ad = W \times 2L_{\min}$.

Source/Drain perimeter is given by:

$ps = pd = 2 \times (W + 2L_{\min})$.

Thus the capacitances contributed by transistors can be accounted for if we know transistor width and length.



When as , ad , ps and pd are specified, the capacitance contributed by these diffused regions is incorporated by the transistor models (and need not be specified separately as a circuit component).

A template file to simulate the inverter is given below. It uses minimum widths for n as well as p channel transistors. Your solution should replace these with appropriate values to meet the delay specification. Notice that the values of area and perimeter of source and drain regions will have to be recalculated when you change the widths.

The .include statement in the template input file given below imports the models from the file models-180nm.

```
* Unit Inverter
.subckt inv supply Inp Output
* This subcircuit defines a CMOS inverter with equal n and p widths
MP1 Output Inp Supply Supply cmosp
+ L=0.18U W=0.24U AD = 0.0864P AS = 0.0864P PD = 1.2U PS = 1.2U
MN1 Output Inp 0 0 cmosn
+ L=0.18U W=0.24U AD = 0.0864P AS = 0.0864P PD = 1.2U PS = 1.2U
.ends

vdd supply 0 dc 1.8

* Device under test
x3 supply Ck dutout inv
```

```

* Load Capacitor
C3 dutout 0 0.05pF

.include models-180nm

*TRANSIENT ANALYSIS with pulse inputs
Vck Ck 0 DC 0 PULSE(0 1.8 0nS 20pS 20pS 4nS 8.0nS)
.tran 1pS 35nS 0nS

.control
run
plot 4.0+V(Ck) V(dutout)
meas tran inrise TRIG v(ck) VAL=0.18 RISE=2 TARG v(Ck) VAL=1.62 RISE=2
meas tran infall TRIG v(ck) VAL=1.62 FALL=2 TARG v(Ck) VAL=0.18 FALL=2
meas tran drise TRIG v(dutout) VAL=0.18 RISE=2 TARG v(dutout) VAL=1.62 RISE=2
meas tran dfall TRIG v(dutout) VAL=1.62 FALL=2 TARG v(dutout) VAL=0.18 FALL=2
.endc
.end

```

Q-1 Design a CMOS inverter which gets a rail to rail square wave as the input with rise/fall times of 20 ps. Your inverter should have equal rise/fall times of $200 + 2 \times nn$ ps, where nn represents the last two digits of your roll number.

The design involves the choice of appropriate widths for n and p channel transistors such that it meets the rise/fall time requirements with the given load. Measure the rise/fall times of the output by finding the time taken by the output to traverse between 10% of V_{DD} and 90% of V_{DD} .

Q-2 Use ng-spice to plot the static transfer characteristics of this inverter by using a DC sweep on the input from 0 to V_{DD} . Determine the static noise margins for it by drawing tangents with slope = -1.

Q-3 Using the above inverter as the base design, apply series-parallel rules to design a logic gate which produces $\overline{A \cdot (B + C)}$ at its output. Find the rise and fall times of this gate for the following input combinations:

- $A = '1', B = '0', C = 0 \rightarrow 1$ and $C = 1 \rightarrow 0$.
- $A = '1', C = '0', B = 0 \rightarrow 1$ and $B = 1 \rightarrow 0$.
- $B = '0', C = '1', A = 0 \rightarrow 1$ and $A = 1 \rightarrow 0$.

Take a logic '1' to be $0.9V_{DD}$ and a logic '0' to be $0.1V_{DD}$.

Q-1 CMOS Inverter

NgSpice Code

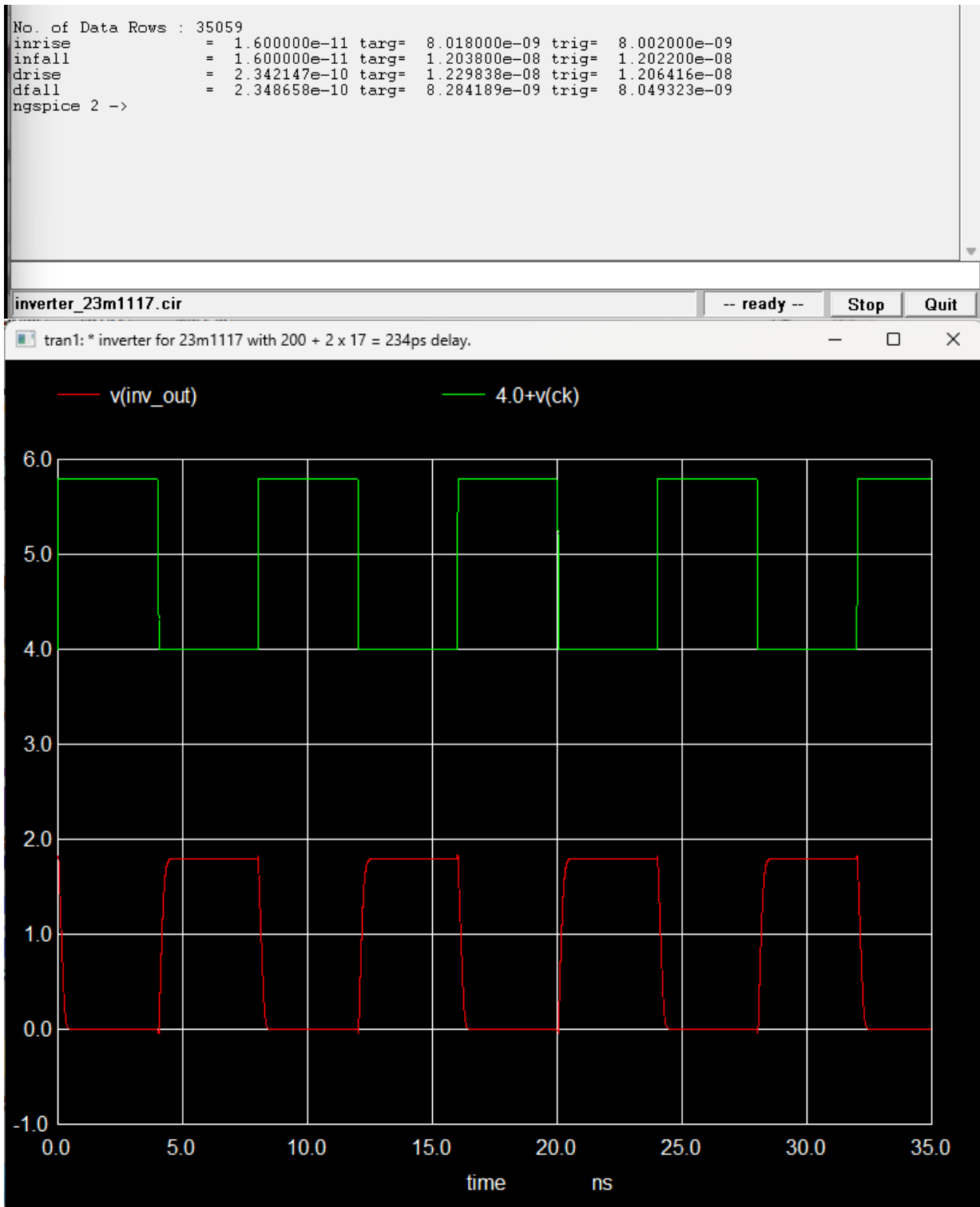
```
1 * Inverter for 23M1117 with 200 + 2 x 17 = 234ps delay.
2
3 *including model files for pMOS and nMOS
4
5 .include models-180nm.txt
6
7 *defining a parameter in order to scale the geometry of pMOS and nMOS
8
9 .param w_p=1.740 w_n=0.595
10 .param l_p=0.18 l_n=0.18
11
12 *defining a circuit component that can be called multiple times
13 *formula used for Area: AD=AS= Wx2Lmin and Perimeter: PD=PS= 2x(W+2Lmin)
14 .subckt inv supply Inp Out
15 MP1 Out Inp Supply Supply cmosp
16 + L={1u*{l_p}} W={{w_p}*1u} AD = {2*{w_p}*{l_p}*{1p}} AS = {2*{w_p}*{l_p}*{1p}}
17   PD = {2*({w_p}+2*{l_p})*1u} PS = {2*({w_p}+2*{l_p})*1u}
18 MN1 Out Inp 0      0      cmosn
19 + L={1u*{l_n}} W={{w_n}*1u} AD = {2*{w_n}*{l_n}*{1p}} AS = {2*{w_n}*{l_n}*{1p}}
20   PD = {2*({w_n}+2*{l_n})*1u} PS = {2*({w_n}+2*{l_n})*1u}
21 .ends
22
23 * Main Supply
24 vdd supply 0 dc 1.8
25 *DUT
26 x1  supply Ck inv_out inv
27 * Load Capacitor
28 C1 inv_out 0 0.05pF
29
30 *TRANSIENT ANALYSIS with pulse inputs
31 Vck  Ck    0 DC 0 PULSE(0 1.8 0nS 20pS 20pS 4nS 8.0nS)
32
33 * transient analysis with 1ps step size untill 35nS with 0nS of delay
34 .tran 1pS 35nS 0nS
35 .control
36 run
37 plot 4.0+V(Ck) V(inv_out)
38 meas tran inrise TRIG v(ck) VAL=0.18 RISE=2 TARG v(Ck) VAL=1.62 RISE=2
39 meas tran infall TRIG v(ck) VAL=1.62 FALL=2 TARG v(Ck) VAL=0.18 FALL=2
40 meas tran drise TRIG v(inv_out) VAL=0.18 RISE=2 TARG v(inv_out) VAL=1.62 RISE=2
41 meas tran dfall TRIG v(inv_out) VAL=1.62 FALL=2 TARG v(inv_out) VAL=0.18 FALL=2
42 .endc
43 .end
```

Output

For pMOS width = $1.740\mu m$ and nMOS width = $0.595\mu m$.

Rise Time = 234.21ps

Fall Time = 234.86ps



Q-2 VTC of CMOS Inverter and Noise Margins

NgSpice code:

```
1 * Inverter for 23M1117 with 200 + 2 x 17 = 234ps delay.
2
3 *including model files for pMOS and nMOS
4
5 .include models-180nm.txt
6
7 *defining a parameter in order to scale the geometry of pMOS and nMOS
8
9 .param w_p=1.740 w_n=0.595
10 .param l_p=0.18 l_n=0.18
11
12 *defining a circuit component that can be called multiple times
13 *formula used for Area: AD=AS= Wx2Lmin and Perimeter: PD=PS= 2x(W+2Lmin)
14 .subckt inv supply Inp Out
15 MP1 Out Inp Supply Supply cmosp
16 + L={1u*{l_p}} W={w_p*1u} AD = {2*{w_p}*{l_p}*{1p}} AS = {2*{w_p}*{l_p}*{1p}}
17   PD = {2*({w_p}+2*{l_p})*1u} PS = {2*({w_p}+2*{l_p})*1u}
18 MN1 Out Inp 0      0      cmosn
19 + L={1u*{l_n}} W={w_n*1u} AD = {2*{w_n}*{l_n}*{1p}} AS = {2*{w_n}*{l_n}*{1p}}
20   PD = {2*({w_n}+2*{l_n})*1u} PS = {2*({w_p}+2*{l_n})*1u}
21 .ends
22
23 * Main Supply
24 vdd supply 0 dc 1.8
25 *DUT
26 x1 supply Ck inv_out inv
27 * Load Capacitor
28 C1 inv_out 0 0.05pF
29 *DC Sweep from 0V to 1.8V with 0.1 steps of increments
30 Vck ck 0 1.8V
31 .DC Vck 0V 1.8V 1mV
32 .control
33 run
34 plot V(ck) V(inv_out)
35 *taking the derivative of the output curve to get to the slope of -1 in order
36   to find noise margins
37 let dv = deriv(V(inv_out))
38
39 meas dc VIL find V(Ck) when dv=-1 fall=1
40 meas dc VIH find V(Ck) when dv=-1 rise=1
41 meas dc VOH find V(inv_out) when V(ck)=VIL
42 meas dc VOL find V(inv_out) when V(ck)=VIH
43
44 let highnoisemargin = VOH-VIH
45 print highnoisemargin
46 let lownoisemargin = VIL - VOL
47 print lownoisemargin
48 .endc
49 .end
```

Output

High noise margin = 714.46mV

Low noise margin = 600.88mV

```
ngspice 40
lownoisemargin = -7.14466e-01
ngspice 18 -> DC.cir

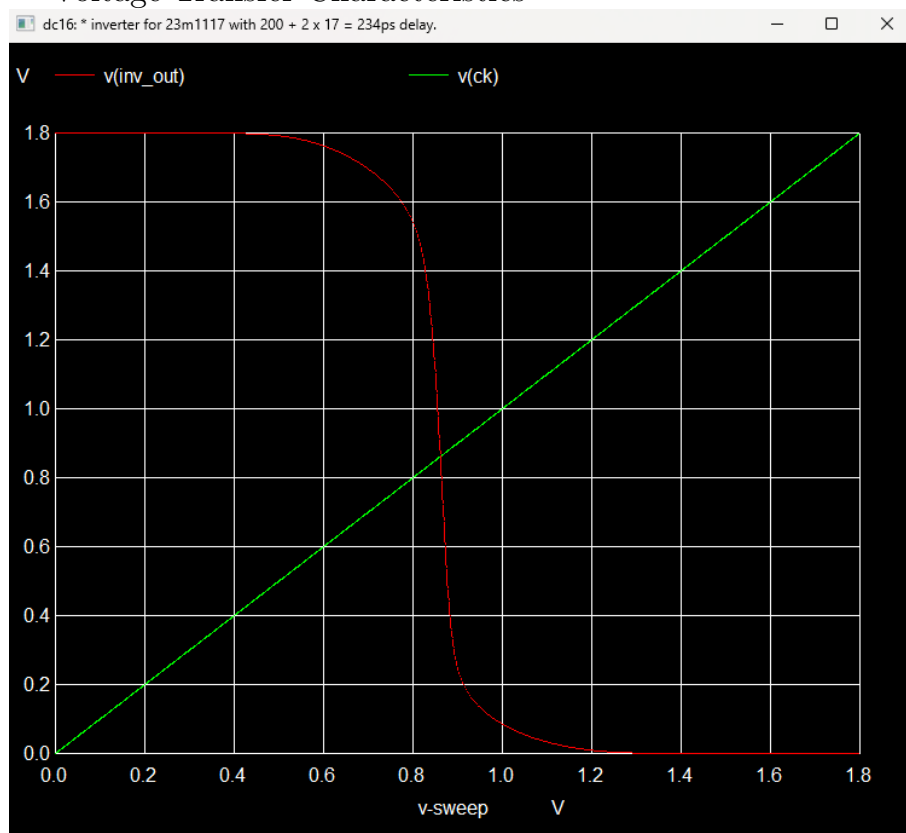
Note: No compatibility mode selected!

Circuit: * inverter for 23m1117 with 200 + 2 x 17 = 234ps delay.
Doing analysis at TEMP = 27.000000 and TNOM = 27.000000

No. of Data Rows : 1801
vil      = 7.121920e-01
vih      = 9.705152e-01
voh      = 1.684981e+00
vol      = 1.113056e-01
highnoisemargin = 7.144658e-01
lownoisemargin = 6.008864e-01
ngspice 19 ->
```

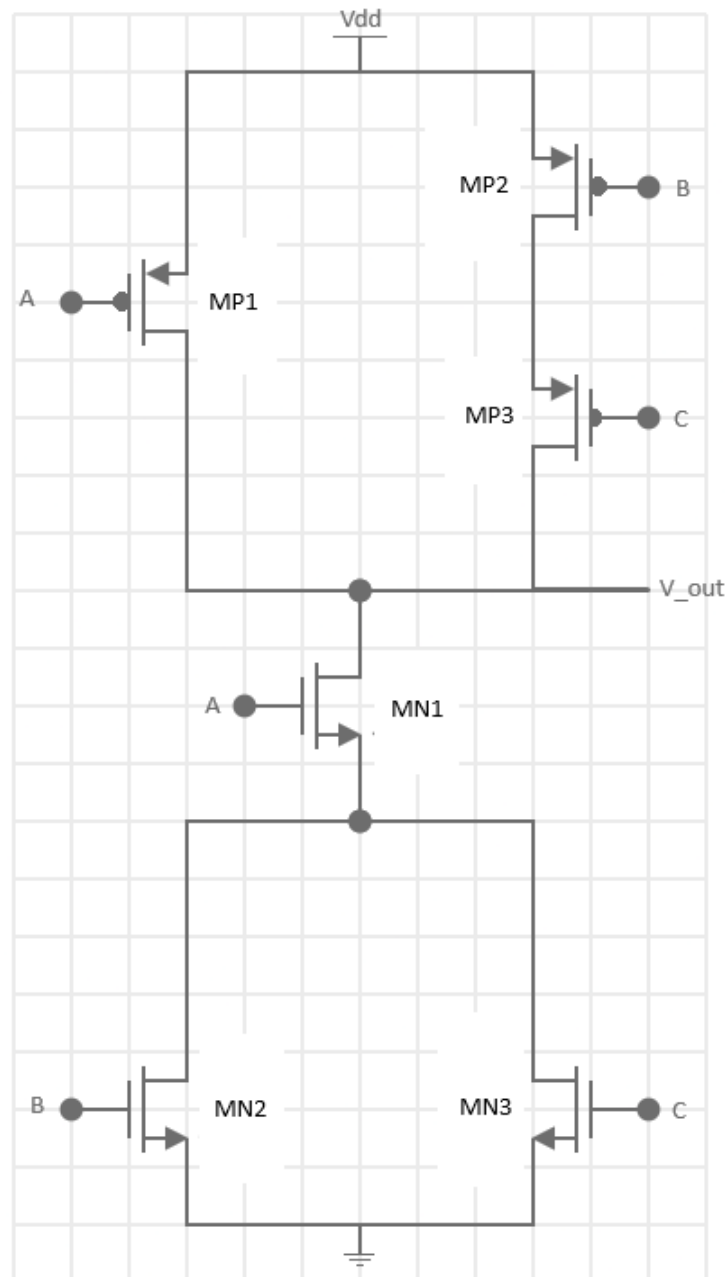
DC.cir -- ready -- Stop Quit

Voltage Transfer Characteristics



Q-3 CMOS Logic Design of $\overline{A.(B + C)}$

- The geometry of MP1 with input A is left as it is.
- The geometry of MP2 and MP3 with input B and C respectively, scaled to 2 times of the CMOS inverter's pMOS width.
- The geometry of MN1, MN2 and MN3 with input A, B, and C respectively, scaled to 2 times of the CMOS inverter's nMOS width.



1) A=1, B=0, C → DC Pulse Input

```

1 * Inverter for 23M1117 with 200 + 2 x 17 = 234ps delay.
2 *including model files for pMOS and nMOS
3 .include models-180nm.txt
4 *main supply
5 Vdd vdd 0 DC 1.8V
6
7 *inputs A = 1, B = 0, and C = Pulse input
8 Va A 0 dc 1.62V
9 Vb B 0 dc 0.18V
10 Vc C 0 DC 0 PULSE(0.18 1.62 0nS 20pS 20pS 4nS 8.0nS)
11
12 *defining a parameter in order to scale the geometry of pMOS and nMOS
13 .param w_p=1.740 w_n=0.595
14 .param l_p=0.18 l_n=0.18
15
16 *MP1 with input A, not scaled!
17 MP1 out A Vdd Vdd cmosp
18 + L={1u*{l_p}} W={{w_p}*1u} AD = {2*{w_p}*{l_p}*{1p}} AS = {2*{w_p}*{l_p}*{1p}}
   PD = {2*({w_p}+2*{l_p})*1u} PS = {2*({w_p}+2*{l_p})*1u}
19
20 *MP2 and MP3 with input B and C respectively, scaled to 2 times of the CMOS
   inverter's pMOS width.
21 MP2 N1 B Vdd Vdd cmosp
22 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
23 MP3 out C N1 N1 cmosp
24 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
25
26 *MN1, MN2 and MN3 with input A, B, and C respectively, scaled to 2 times of the
   CMOS inverter's nMOS width.
27 MN1 Out A N2 N2 cmosn
28 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
29 MN2 N2 B 0 0 cmosn
30 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
31 MN3 N2 C 0 0 cmosn
32 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
33
34 *load capacitor
35 C3 out 0 0.05pF
36
37 *TRANSIENT ANALYSIS with pulse inputs
38 .tran 1pS 35nS 0nS
39 .control
40 run
41 plot V(out) V(A)+12 V(B)+8 V(C)+4
42 meas tran drise TRIG v(out) VAL=0.18 RISE=2 TARG v(out) VAL=1.62 RISE=2
43 meas tran dfall TRIG v(out) VAL=1.62 FALL=2 TARG v(out) VAL=0.18 FALL=2
44 .endc
45 .end

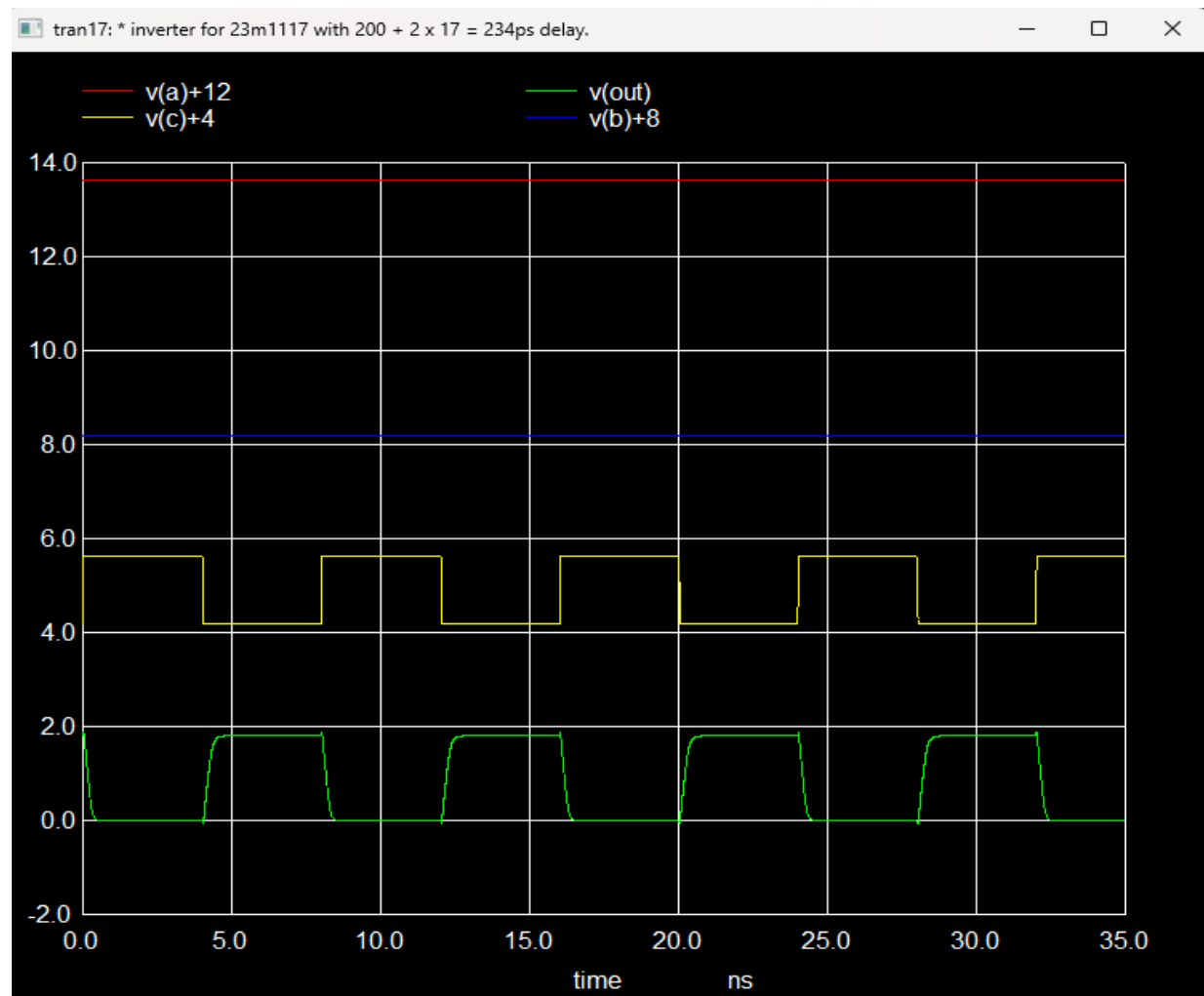
```

Rise time = 300ps, and Fall time = 256ps

ngspice 40	
Node	Voltage
-----	-----
vdd	1.8
a	1.62
b	0.18
c	0.18
out	1.79999
n1	1.8
n2	1.38894
vc#branch	0
vb#branch	0
va#branch	0
vdd#branch	-4.00156e-09

No. of Data Rows : 35059
drise = 3.004081e-10 targ= 1.237838e-08 trig= 1.207798e-08
dfall = 2.567697e-10 targ= 8.322196e-09 trig= 8.065427e-09
ngspice 23 ->

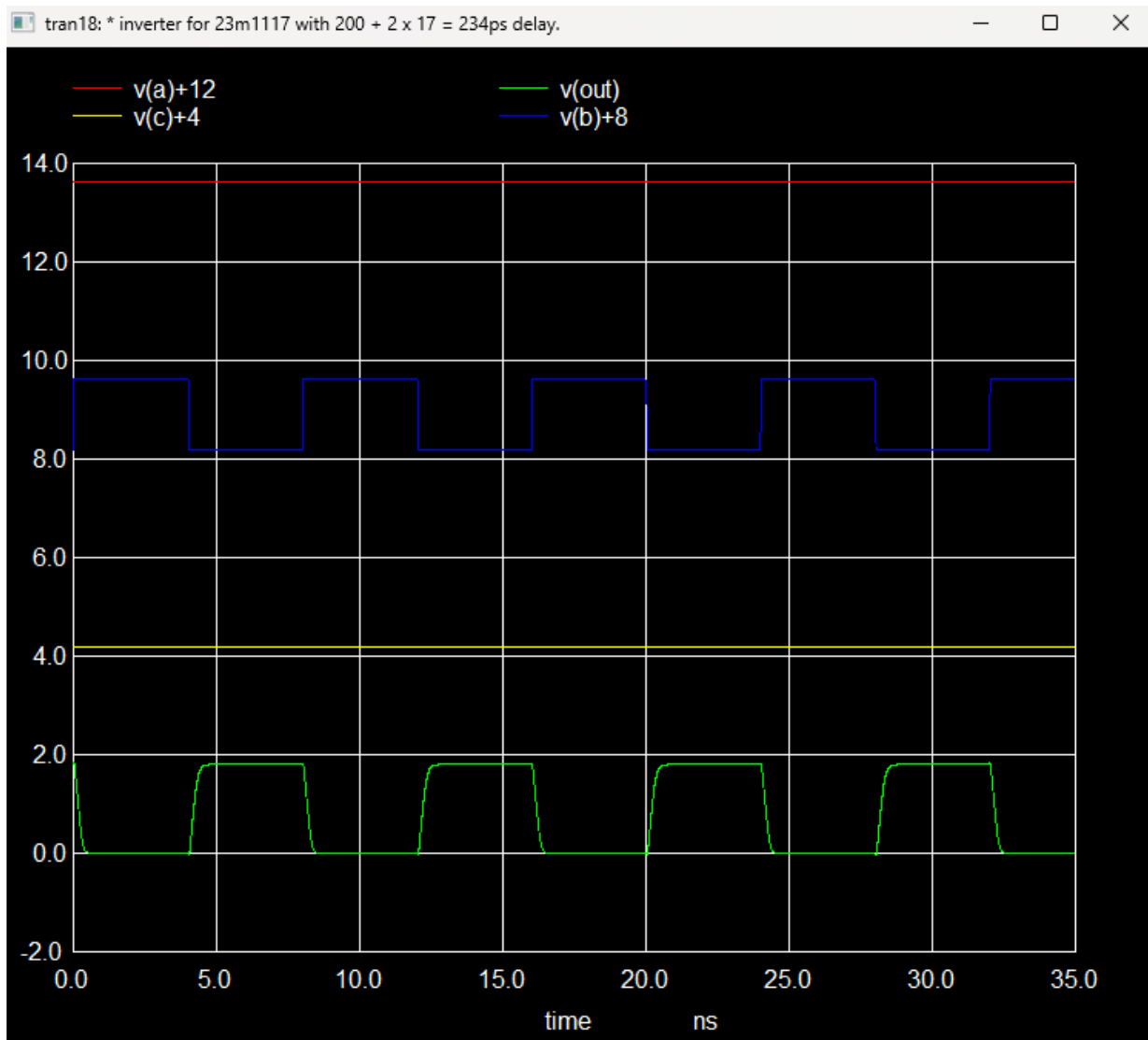
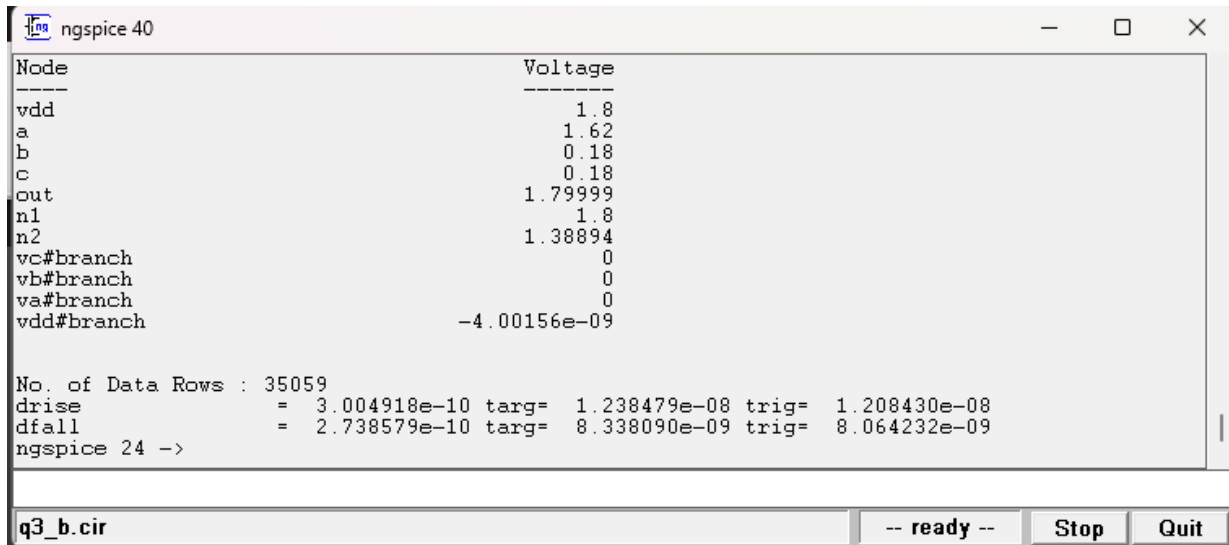
q3.cir -- ready -- Stop Quit



2) A=1, B → DC Pulse Input, C=0

```
1 * Inverter for 23M1117 with 200 + 2 x 17 = 234ps delay.
2 *including model files for pMOS and nMOS
3 .include models-180nm.txt
4 *main supply
5 Vdd vdd 0 DC 1.8V
6
7 *inputs A = 1, B = Pulse input, and C = 0.
8 Va A 0 dc 1.62V
9 Vb B 0 dc 0 PULSE(0.18 1.62 0nS 20pS 20pS 4nS 8.0nS)
10 Vc C 0 DC 0.18V
11
12 *defining a parameter in order to scale the geometry of pMOS and nMOS
13 .param w_p=1.740 w_n=0.595
14 .param l_p=0.18 l_n=0.18
15
16 *MP1 with input A, not scaled!
17 MP1 out A Vdd Vdd cmosp
18 + L={1u*{l_p}} W={{w_p}*1u} AD = {2*{w_p}*{l_p}*{1p}} AS = {2*{w_p}*{l_p}*{1p}}
   PD = {2*({w_p}+2*{l_p})*1u} PS = {2*({w_p}+2*{l_p})*1u}
19
20 *MP2 and MP3 with input B and C respectively, scaled to 2 times of the CMOS
   inverter's pMOS width.
21 MP2 N1 B Vdd Vdd cmosp
22 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
23 MP3 out C N1 N1 cmosp
24 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
25
26 *MN1, MN2 and MN3 with input A, B, and C respectively, scaled to 2 times of the
   CMOS inverter's nMOS width.
27 MN1 Out A N2 N2 cmosn
28 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
29 MN2 N2 B 0 0 cmosn
30 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
31 MN3 N2 C 0 0 cmosn
32 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
33
34 C3 out 0 0.05pF
35
36
37 *TRANSIENT ANALYSIS with pulse inputs
38
39
40 .tran 1pS 35nS 0nS
41 .control
42 run
43 plot V(out) V(A)+12 V(B)+8 V(C)+4
44 meas tran drise TRIG v(out) VAL=0.18 RISE=2 TARG v(out) VAL=1.62 RISE=2
45 meas tran dfall TRIG v(out) VAL=1.62 FALL=2 TARG v(out) VAL=0.18 FALL=2
46
47 .endc
48 .end
```

Rise time = 300ps, and Fall time = 273ps



3) A → DC Pulse Input, B=0, C=1

```
1 * Inverter for 23M1117 with 200 + 2 x 17 = 234ps delay.
2 *including model files for pMOS and nMOS
3 .include models-180nm.txt
4 *main supply
5 Vdd vdd 0 DC 1.8V
6
7 Va A 0 dc PULSE(0.18 1.62 0nS 20pS 20pS 4nS 8.0nS)
8 Vb B 0 dc 0.18
9 Vc C 0 DC 1.62V
10
11 *defining a parameter in order to scale the geometry of pMOS and nMOS
12
13 .param w_p=1.740 w_n=0.595
14 .param l_p=0.18 l_n=0.18
15
16 *MP1 with input A, not scaled!
17 MP1 out A Vdd Vdd cmosp
18 + L={1u*{l_p}} W={{w_p}*1u} AD = {2*{w_p}*{l_p}*{1p}} AS = {2*{w_p}*{l_p}*{1p}}
   PD = {2*({w_p}+2*{l_p})*1u} PS = {2*({w_p}+2*{l_p})*1u}
19
20 *MP2 and MP3 with input B and C respectively, scaled to 2 times of the CMOS
   inverter's pMOS width.
21 MP2 N1 B Vdd Vdd cmosp
22 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
23 MP3 out C N1 N1 cmosp
24 + L={1u*{l_p}} W={{w_p}*2u} AD = {2*2*{w_p}*{l_p}*{1p}} AS = {2*2*{w_p}*{l_p}
   }*{1p}} PD = {2*(2*{w_p}+2*{l_p})*1u} PS = {2*(2*{w_p}+2*{l_p})*1u}
25
26 *MN1, MN2 and MN3 with input A, B, and C respectively, scaled to 2 times of the
   CMOS inverter's nMOS width.
27 MN1 Out A N2 N2 cmosn
28 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
29 MN2 N2 B 0 0 cmosn
30 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
31 MN3 N2 C 0 0 cmosn
32 + L={1u*{l_n}} W={{w_n}*2u} AD = {2*2*{w_n}*{l_n}*{1p}} AS = {2*2*{w_n}*{l_n}
   }*{1p}} PD = {2*(2*{w_n}+2*{l_n})*1u} PS = {2*(2*{w_n}+2*{l_n})*1u}
33
34 *load capacitor
35 C3 out 0 0.05pF
36
37 *TRANSIENT ANALYSIS with pulse inputs
38 .tran 1pS 35nS 0nS
39 .control
40 run
41 plot V(out) V(A)+12 V(B)+8 V(C)+4
42 meas tran drise TRIG v(out) VAL=0.18 RISE=2 TARG v(out) VAL=1.62 RISE=2
43 meas tran dfall TRIG v(out) VAL=1.62 FALL=2 TARG v(out) VAL=0.18 FALL=2
44 .endc
45 .end
```

Risetime = 309ps, and Fall time = 256ps

